



# Lecture 16: Analog Circuits

VE311 Electronic Circuits

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2023 Fall



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# Recap of Last Lecture



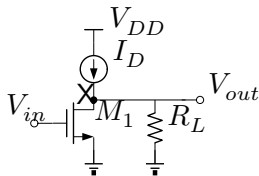
- Source Follower

# Topic to be covered



- Source Follower
- Emitter Follower
- Common Gate

## CS + Source Follower

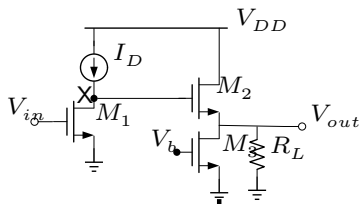


$$A_v = -gm_1 (r_{o1} \parallel R_L)$$

- Voltage gain severely reduced when  $R_L$  very small

$$A_v = -gm_1 r_{o1} \times gm_2 \left( r_{o2} \parallel \frac{1}{gm_2 + g_{mb2}} \parallel r_{o3} \parallel R_L \right) \quad (1)$$

- Voltage gain maintained when  $R_L$  very small



## Source Follower Example

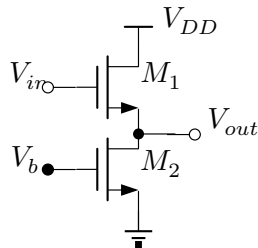


$$(W/L)_1 = 20/0.5, I_D = 0.2 \text{ mA}, V_{THO} = 0.6 \text{ V}, 2\Phi_F = 0.7 \text{ V}, \mu_n C_{ox} = 50 \mu\text{A}/\text{V}^2, \gamma = 0.4 \text{ V}^{1/2} \text{ and } \lambda = 0$$

(a) Calculate  $V_{out}$  for  $V_{in} = 1.2 \text{ V}$ .

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{in} - V_{out} - V_{THO})^2 \quad (2)$$

$$\rightarrow V_{out} = 0.153 \text{ V} \quad (3)$$

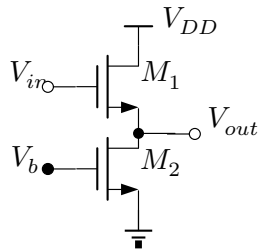


# Source Follower Example



$$V_{TH1} = V_{TH0} + \gamma \left( \sqrt{2\Phi_F + V_{out}} - \sqrt{2\Phi_F} \right) = 0.635 \text{ V} \quad (4)$$

$$\rightarrow V_{out} \approx 0.118 \text{ V} \quad (5)$$



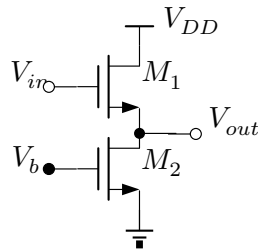
# Source Follower Example



(b) Minimum  $(W/L)_2$  for which  $M_2$  remains saturated.

$$V_{out} = 0.118 \text{ V} \geq V_{GS2} - V_{TH2} \quad (6)$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS2} - V_{TH2})^2 \rightarrow \left( \frac{W}{L} \right)_2 \geq \frac{283}{0.5} \quad (7)$$



# Source Follower Example

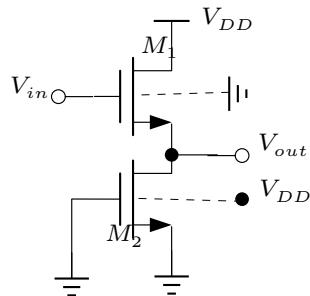


Calculate the small signal voltage gain of the circuit below.

$$G_m = g_{m1} \quad (8)$$

$$R_{out} = \frac{1}{g_{m1} + g_{mb1}} \parallel r_{o1} \parallel \frac{1}{g_{m2} + g_{mb2}} \parallel r_{o2} \quad (9)$$

$$A_v = G_m R_{out} \quad (10)$$





# Emitter Follower



Common Collector

Reading: Sedra & Smith, 8th Ed.: 7.3 (BJT CC)

Short-Circuit Current  
Gain

$$A_{ix} \equiv \frac{i_o}{i_i} \big|_{v_o=0} \quad (A/A)$$

$$R_i = 0$$

Short-Circuit  
Transconductance

$$R_o = \infty$$

$$R_i = \infty$$

$$G_m \equiv \frac{i_o}{v_i} \big|_{v_o=0} \quad (A/V)$$

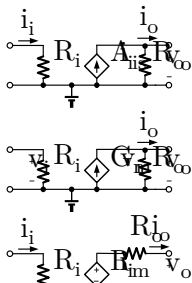
$$R_o = \infty$$

$$R_i = 0$$

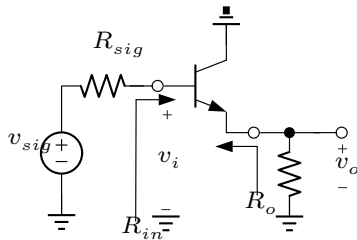
Short-Circuit

$$R_o = 0$$

Current Amplifier  
Transconductance  
Amplifier  
Transresistance  
Amplifier

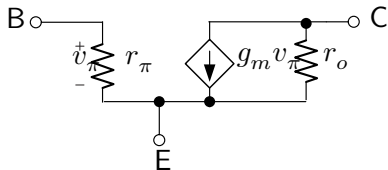


# Emitter Follower

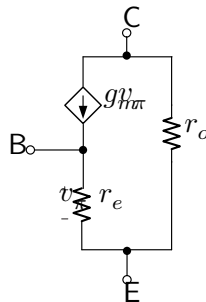


- Transistor is biased to be in the FAR using the same biasing technique for CE amplifier.

# Emitter Follower impedance



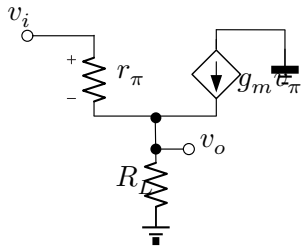
Textbook Pi-model



Textbook T-model

$$g_m = \frac{\alpha}{r_e} r_\pi = (\beta + 1) r_e$$

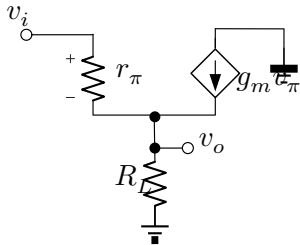
# Emitter Follower impedance



$$R_{in} = r_{\pi} + (\beta + 1)R_L \quad (11)$$

$$R_{out} = r_{\pi} \parallel (1/gm) \quad (12)$$

# Emitter Follower gain



$$\frac{v_o}{v_i} = \frac{R_L}{\frac{1}{g_m + 1/r_\pi} + R_L} \quad (13)$$

# CC Amplifier with Biasing Circuit



- No collector resistor
- no bypass capacitor
- Biasing scheme remains the same.
- Output taken out at the emitter.

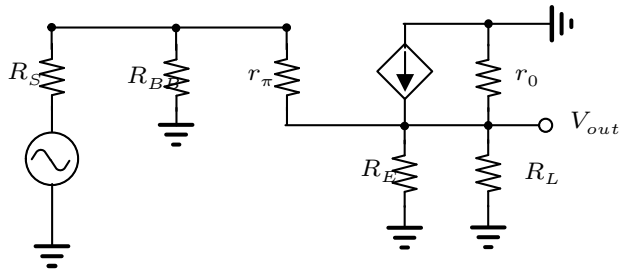
# CC Amplifier with Biasing Circuit



# CC Amplifier with Biasing Circuit

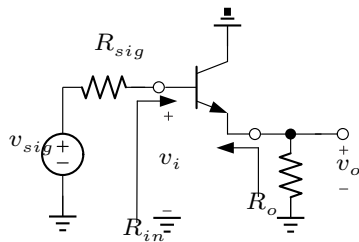


Use the current relationship of  $i_b$  and  $i_c$





# CC Amplifier with Biasing Circuit



$$\frac{v_i}{v_{sig}} = \frac{R_{in}}{R_{in} + R_{sig}} = \frac{(\beta + 1)(r_e + R_L)}{(\beta + 1)(r_e + R_L) + R_{sig}} \quad (14)$$

$$G_v \equiv \frac{v_o}{v_{sig}} = \frac{v_i}{v_{sig}} \times A_v \quad (15)$$

$$G_v = \frac{(\beta + 1)R_L}{(\beta + 1)R_L + (\beta + 1)r_e + R_{sig}} \quad (16)$$

# CC Amplifier Swing



- Assume output is a sinusoid with peak voltage of  $V_P$

# CC Amplifier Swing



- Emitter voltage can get to within  $V_{CESAT}$  of the supply voltage before transistor enters saturation, therefore the maximum output voltage is  $V_{CC} - V_{CESAT} - V_{EQ}$ .

## CC Amplifier Swing



Total emitter current is given by:

$$i_E = \frac{V_{EQ}}{R_E} + \frac{v_p}{R_E} + \frac{v_p}{R_L}$$

$$i_E = \frac{V_{EQ}}{R_E} - \frac{V_P}{R_E} - \frac{V_P}{R_L} = 0$$

$$\frac{V_{EQ}}{R_E} - \frac{V_P (R_L + R_E)}{R_L R_E} = 0$$

$$V_P = \frac{V_{EQ} (R_L)}{R_L + R_E}$$

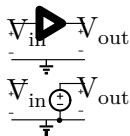
$$= V_{EQ} / \left( 1 + \frac{R_E}{R_L} \right)$$

$$V_{E \min} = V_{EQ} - V_P = \frac{V_{EQ} (R_E)}{R_L + R_E} = V_{EQ} / \left( 1 + \frac{R_L}{R_E} \right)$$

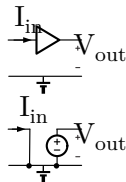
# Ideal Amplifier



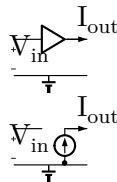
Voltage Amp.



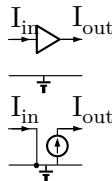
Transimpedance  
Amp.



Transconductance  
Amp.

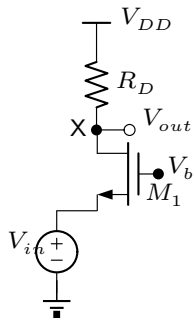


Current Amp.



- For converting and amplifying small-signal current to voltages, common-gate provides low input impedance and moderate gain, but relatively large output impedance.

# Common-Gate ( $\lambda = 0, \gamma \neq 0$ )



- $V_{in} > V_b - V_{TH} \rightarrow M_1$  Off
- $V_{out} = V_{DD}$
- $V_b - V_{TH} > V_{in} > V_{in1} \rightarrow M_1$  in Saturation

$$V_{out} = V_{DD} - R_D \frac{1}{2} \mu_n C_{ox} \frac{w}{L} (V_b - V_{in} - V_{TH})^2 \quad (17)$$

# Common-Gate



At the boundary of triode/saturation:

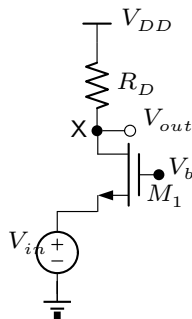
$$V_{out} = V_b - V_{TH} \quad (18)$$

$$= V_{DD} - R_D \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_b - V_{in1} - V_{TH})^2 \quad (19)$$

$$V_{in} < V_{in1} \rightarrow M_1 \text{ in Triode} \quad (20)$$

Triode region equation as follows:

$$V_{out} = V_{DD} - R_D \mu_n C_{ox} \frac{W}{L} \left[ (V_b - V_{in} - V_{TH}) (V_{out} - V_{in}) - \frac{1}{2} (V_{out} - V_{in})^2 \right] \quad (21)$$



## Common-Gate ( $\lambda = 0, \gamma \neq 0$ )



$$V_b - V_{TH} > V_{in} > V_{in1} \rightarrow M_1 \text{ in Saturation} \quad (22)$$

$$V_{out} = V_{DD} - R_D \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_b - V_{in} - V_{TH})^2 \quad (23)$$

$$\frac{\partial V_{out}}{\partial V_{in}} = -R_D \frac{1}{2} \mu_n C_{ox} \frac{W}{L} 2 (V_b - V_{in} - V_{TH}) \left( -1 - \frac{\partial V_{TH}}{\partial V_{in}} \right) \quad (24)$$

$$= R_D \mu_n C_{ox} \frac{W}{L} (V_b - V_{in} - V_{TH}) \left( 1 + \frac{\partial V_{TH}}{\partial V_{in}} \right) \quad (25)$$

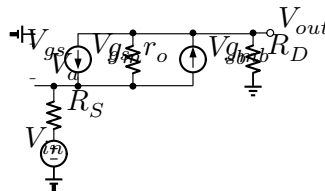
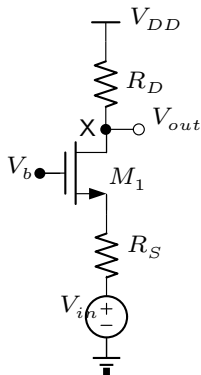
$$A_v = \frac{\partial V_{out}}{\partial V_{in}} = R_D g_m (1 + \eta) \quad (26)$$

- $g_m$  is a function of  $I_D$  and  $\eta$  is a function of  $V_{SB}$ .
- $A_v$  is not quite linear.





# Common-Gate ( $\lambda = 0, \gamma \neq 0$ Small-signal)



$$G_m = \frac{(g_m + g_{mb})r_o + 1}{r_o + R_S + (g_m + g_{mb})r_o R_S}$$

$$R_{out} = R_D \parallel [r_o + R_S + (g_m + g_{mb})r_o R_S]$$

$$A_v = \frac{(g_m + g_{mb})r_o + 1}{r_o + R_S + (g_m + g_{mb})r_o R_S + R_D} R_D \approx R_D g_m (1 + \eta)$$

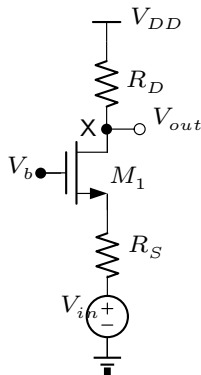
## Common-Gate ( $\lambda = 0, \gamma \neq 0$ Small-signal)



## Common-Gate SS gain



Transconductance gain: use Norton equivalent



# Common-Gate SS gain



Output Impedance: SS model